



# DCR1950C52

# **Phase Control Thyristor**

DS5187-3 January 2014 (LN31254)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR1950C52* DCR1950C50 DCR1950C48	5200 5000 4800	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM}  t_p &= 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} &= \\ V_{DRM}  \&  V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. \*5000V @ -40°C, 5200V @ 0°C

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR1950C52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

$V_{DRM}$	5200V
$I_{T(AV)}$	1950A
I <sub>TSM</sub>	26250A
dV/dt*	1500V/µs
dI/dt	300A/μs

## \* Higher dV/dt selections available

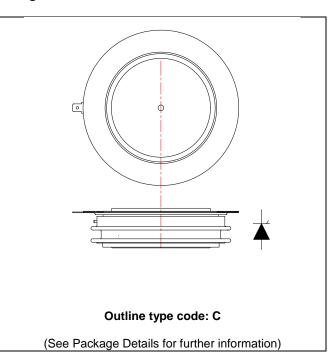


Fig. 1 Package outline



## **CURRENT RATINGS**

## $T_{case} = 60$ °C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1950	А
I <sub>T(RMS)</sub>	RMS value	-	3060	А
I <sub>T</sub>	Continuous (direct) on-state current	-	3000	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	26.25	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	3.45	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0101	°C/W
		Single side cooled	Anode DC	-	0.0176	°C/W
			Cathode DC	-	0.0239	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 37kN	Double side	-	0.0025	°C/W
		(with mounting compound)	Single side	-	0.005	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			33.0	41.0	kN





## **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	300	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
V <sub>T(TO)</sub>	Threshold voltage – Low level	500A to 2000A at T <sub>case</sub> = 125	5°C	-	0.932	V
	Threshold voltage – High level	2000A to 7000A at T <sub>case</sub> = 125°C		-	1.100	V
r <sub>T</sub>	On-state slope resistance – Low level	500A to 2000A at T <sub>case</sub> = 125°C		-	0.434	mΩ
	On-state slope resistance – High level	2000A to 7000A at T <sub>case</sub> = 125°C		-	0.346	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, dI/dt	= 1A/μs,	700	1100	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Q <sub>S</sub>	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt - 1A/\mu s$ ,		1200	2800	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	Α
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I <sub>T</sub> = 5A	-	300	mA



### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	350	mA
$I_{GD}$	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

### **CURVES**

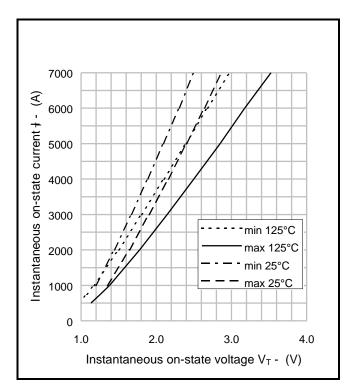


Fig.2 Maximum & minimum on-state characteristics

**V<sub>TM</sub> EQUATION** 

 $V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = -0.142705

B = 0.203033

C = 0.000358

D = -0.00751

these values are valid for  $T_j$  = 125°C for  $I_T$  100A to 7200A

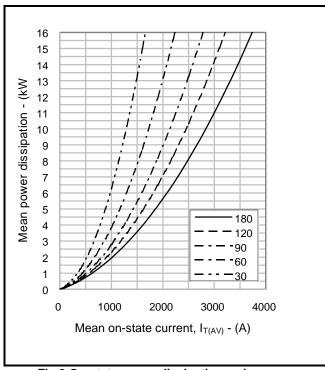


Fig.3 On-state power dissipation - sine wave

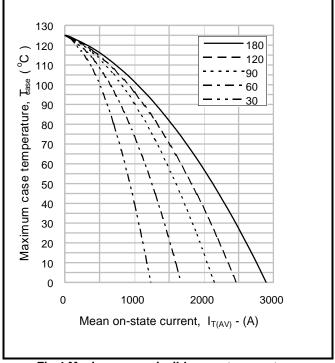


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

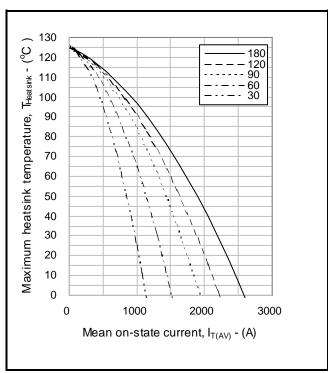


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

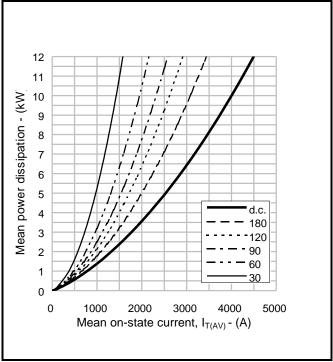


Fig.6 On-state power dissipation - rectangular wave

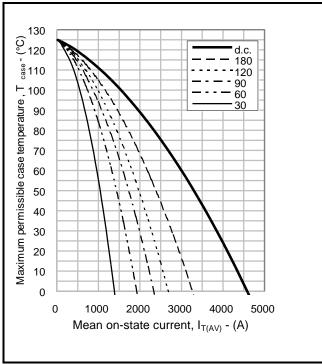


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

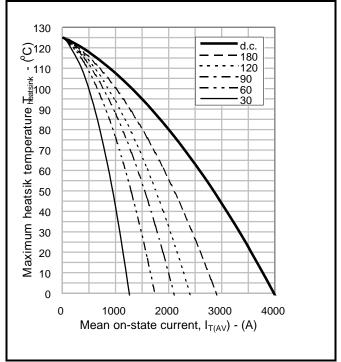
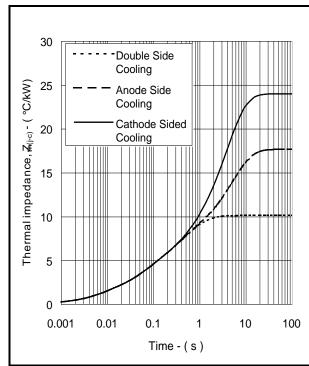


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	1.1043	2.576	4.5096	1.9009
	T <sub>i</sub> (s)	0.006176	0.0517916	0.3820376	1.06
Anode side cooled	R <sub>i</sub> (°C/kW)	1.0977	2.4566	4.0469	9.9994
	T <sub>i</sub> (s)	0.006153	0.050142	0.3129407	5.27
Cathode side cooled	R <sub>i</sub> (°C/kW)	1.1519	2.8926	2.4064	17.4793
	T <sub>i</sub> (s)	0.006389	0.0582953	0.3775516	3.97

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$  [1]

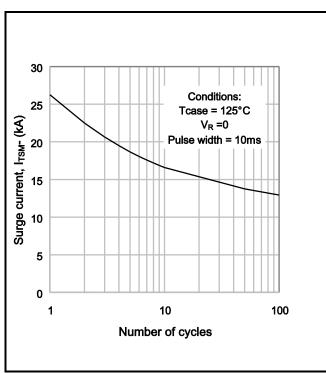
 $\Delta R_{\text{th(j-c)}}$  Conduction

Tables show the increments of thermal resistance  $R_{\text{th(j-c)}}$  when the device operates at conduction angles other than d.c.

	Double side co	ooling			Anode Side	Cooling	
	$\Delta Z_{th}$ (	∆Z <sub>th</sub> (z)			$\Delta Z_{th}(z)$		
θ°	sine.	rect.		θ°	sine.	rect.	
180	1.95	1.26		180	1.95	1.26	
120	2.32	1.89		120	2.32	1.89	
90	2.74	2.27		90	2.74	2.27	
60	3.14	2.70		60	3.14	2.70	
30	3.46	3.19		30	3.46	3.19	

Š	Cathode Sided Cooling				
	$\Delta Z_{th}$ (z)				
θ°	sine.	rect.			
180	1.95	1.26			
120	2.31	1.88			
90	2.72	2.26			
60	3.12	2.68			
30	3.43	3.17			

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)



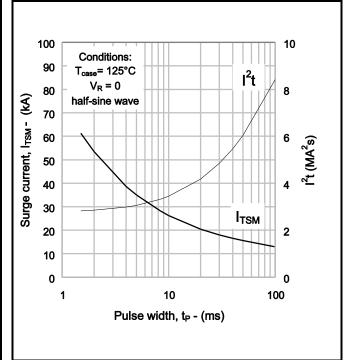
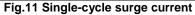


Fig.10 Multi-cycle surge current



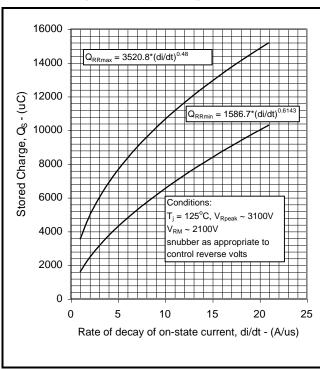


Fig.12 Stored Charge

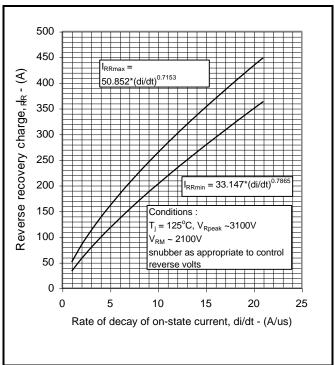


Fig.13 Reverse recovery current

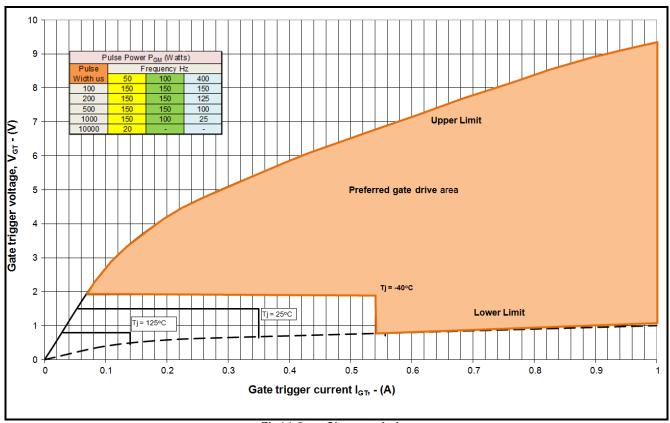


Fig14 Gate Characteristics

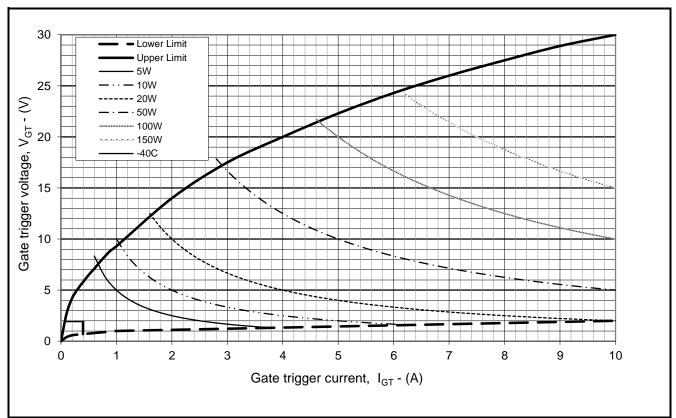


Fig. 15 Gate characteristics



### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

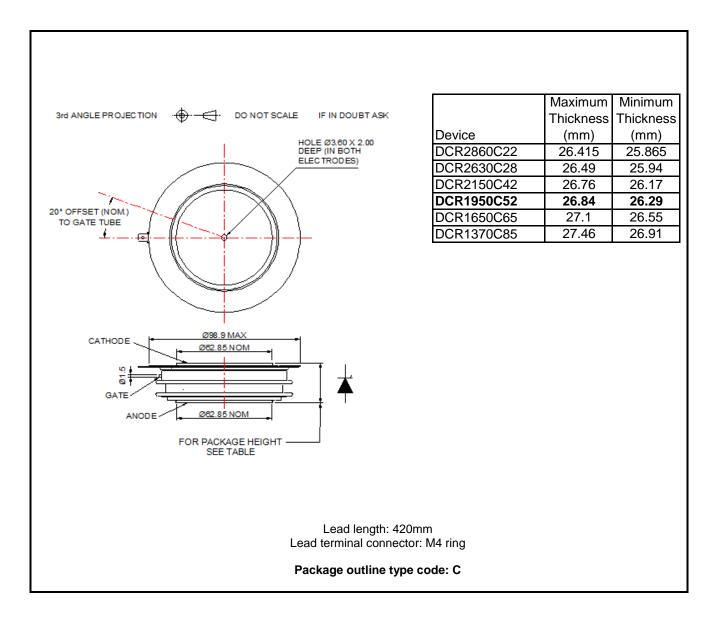


Fig.16 Package outline





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#### **HEADQUARTERS OPERATIONS**

DYNEX SEMICONDUCTOR LIMITED Doddington Road, Lincoln, Lincolnshire, LN6 3LF

United Kingdom.

No Annotation:

Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

#### **CUSTOMER SERVICE**

Phone: +44 (0) 1522 502753 / 502901 Fax: +44 (0) 1522 500020 e-mail: power\_solutions@dynexsemi.com

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